

positions of the remaining hydrogen atoms were calculated (P-C-H and H-C-H = 109.5°). Refinement of all non-hydrogen atoms anisotropically resulted in $R_w = 0.068$; this small improvement (for 85 extra variables) combined with the large deviations in the anisotropic thermal parameters indicated that the data were not sufficiently accurate to warrant this degree of refinement. At this point a correction for the 1.5% decay of the three standard reflections was applied, but as expected, the effect was small. Final refinement with anisotropic thermal parameters for tungsten, antimony, and phosphorus only and recalculation of the hydrogen atom positions gave the residuals in Table X. The largest peaks on the final difference map were all due to heavy-atom noise, being randomly oriented about the tungsten atom at distances of 1.01-1.21 and 0.96-1.10 Å, respectively. Finally, there is one relatively short intermolecular contact of 2.30 Å between F(6) and H(10) (the hydrogen atom on C(10)).

Structure Determination of 3c. Crystals were obtained by layering hexanes onto a cold solution of 3c in CH₂Cl₂ and allowing the mixture to stand at -40 °C overnight. The successful solution of the structure ultimately justified the initial assumption of space group $P\bar{1}$. A 1.0% decay in the intensities of the three standard reflections was observed over the course of the data collection, but no correction was applied. Positions and isotropic thermal parameters for the 35 non-hydrogen atoms refined as above to $R_w = 0.076$. Positions for the hydrogen atoms were calculated (C-H = 1.00 Å), and further isotropic refinement gave $R_w = 0.063$. An absorption correction was then applied by using an $8 \times 8 \times 8$ grid. Refinement with anisotropic thermal parameters for all non-hydrogen atoms gave the residuals in Table X. The largest peaks on the final difference map were all due to heavy-atom noise, being randomly oriented about the tungsten and antimony atoms at distances of 0.99-1.10 Å and 1.10-1.16 Å, respectively.

Structure Determination of 5. Crystals of 5 were grown at -40 °C as described above for 3c. Inspection of the data showed that reflections having $0k0$, $k = 2n + 1$, and $h0l$, $h + l = 2n + 1$, were systematically absent, consistent only with space group $P2_1/n$. A correction for the 3.7% decay of the three standard reflections was applied. Positions and isotropic thermal parameters for the 18 non-hydrogen atoms refined as above to $R_w = 0.062$. An absorption correction was then applied by using an $8 \times 8 \times 8$ grid. Refinement with anisotropic thermal parameters for all non-hydrogen atoms was carried out. A difference map allowed the location of five hydrogen atoms on the three methyl carbons, and the positions of the remaining hydrogen atoms were calculated (P-C-H and H-C-H = 109.5°). Final refinement of all non-hydrogen atoms using

anisotropic thermal parameters gave the residuals in Table X. The largest peaks on the final difference map were all due to heavy-atom noise, being randomly oriented about the tungsten atom at distances of 0.97-1.56 Å.

Structure Determination of 6. Crystals of 6 were grown at -40 °C as described above for 3c. Inspection of the data showed that reflections having $0k0$, $k = 2n + 1$, and $h0l$, $h + l = 2n + 1$, were systematically absent, consistent only with space group $P2_1/n$. A correction for the 2.5% decay of the three standard reflections was applied. Positions and isotropic thermal parameters for the 20 non-hydrogen atoms refined as above to $R_w = 0.103$. An absorption correction was then applied by using an $8 \times 8 \times 8$ grid. Refinement with anisotropic thermal parameters for the three heaviest atoms gave $R_w = 0.078$. A difference map was used to locate one hydrogen atom on each of the methyl groups, and the positions of the remaining hydrogen atoms were then calculated as above. Refinement of all non-hydrogen atoms using anisotropic thermal parameters gave the residuals in Table X. The largest peaks on the final difference map were all due to heavy-atom noise, being randomly oriented about the tungsten atom at distances of 0.09-1.16 Å.

Acknowledgment. We wish to thank Professor C. E. Strouse and Dr. C. B. Knobler for their help with the X-ray structure determinations, Professor K. N. Trueblood for assistance with his thermal motion analysis program, Professor J. W. Faller (Yale University) for helpful discussions, Andrew Fortney for providing a sample of 3b, and Peter Bonnesen for assistance with several ¹⁹F NMR spectra. Financial support was provided by the donors of the Petroleum Research Fund, administered by the American Chemical Society, and by the Chevron Research Co., the UCLA Committee on Research, and a Biomedical Research Support Grant.

Supplementary Material Available: Tables of full crystallographic data for 3b, 3c, 5, and 6, positional parameters, bond distances and angles, and temperature factors for 3c, 5, and 6, and input frequencies and output force constants for 13 compounds and details of the calculation of the Cotton-Kraihanzel force constants (25 pages); tables of structure factors for 3c, 5, and 6 (33 pages). The X-ray data for 3b is available as supplementary material to ref 15. Ordering information is given on any current masthead page.

Notes

Contribution from Dow Corning Corporation,
Midland, Michigan 48686

A New Synthetic Route to Fluorodisilanes via Selective Reduction of Halofluorodisilanes

John J. D'Errico[†] and Kenneth G. Sharp*

Received September 7, 1988

Our primary interest in fluorodisilanes was as potential molecular precursors to amorphous silicon films^{1,2} containing hydrogen and fluorine. The use of fluorodisilanes for this purpose eliminates the need for precursor gas mixtures such as SiF₄/SiH₄.³ In addition, lower deposition temperatures are required when compared to the case for compounds such as SiF₂H₂.⁴

Several routes to fluorodisilanes have been reported. Mixtures of SiF₂HSiH₃ and SiF₃SiH₃ were generated from the reaction of SiCl₂HSiH₃ with SbF₃.⁵ Fluorodisilane is obtained via the cleavage of Si-O or Si-N bonds in (Si₂H₅)₂O or (Si₂H₅)₃N by BF₃.^{6,7} Also, direct current ("ozonizer") plasma synthesis of the symmetrical disilanes 1,2-difluorodisilane and 1,1,2,2-tetrafluorodisilane via coupling reactions of the radicals derived from

the monosilanes SiH₃F and SiH₂F₂ has been reported.⁵ This route has the disadvantages of involving slow, low-yield reactions and the difficulty of preparing pure SiFH₃.⁸

This report describes the reactions of bromofluoro- or chlorofluorodisilanes with Me₃SnH. These reactions are characterized by the selective reduction of Si-Cl or Si-Br bonds without cleavage of Si-F or Si-Si bonds.

Experimental Section

Materials and Manipulations. All manipulations were conducted by using a recirculating drybox (N₂ atmosphere), Schlenk techniques (Ar atmosphere), and a grease-free glass vacuum line (background pressure <10⁻⁴ Torr). Trimethyltin chloride, SbF₃, [(CH₃)₂CHCH₂]₂AlH (DI-BAL-H, Aldrich Chemical Co.), and VITRIDE (70% NaAlH₂(OCH₂-CH₂OCH₃)₂ in toluene, Hexcel Specialty Chemicals) were used as obtained. Trimethyltin hydride was prepared from the LiAlH₄ reduction

- (1) Stutzmann, M.; Jackson, W. B.; Tsai, C. C. *J. Non-Cryst. Solids* **1985**, *77&78*, 363.
- (2) Janai, M.; Weil, R.; Pratt, B. *Phys. Rev. B* **1985**, *31*, 5311.
- (3) Uesugi, T.; Hisanori, I.; Matsumura, H. *Jpn. J. Appl. Phys., Part 1* **1985**, *24*, 909.
- (4) Sharp, K. G.; D'Errico, J. J. U.S. Patent 4 762 808, Aug 9, 1988.
- (5) Drake, J. E.; Westwood, N. P. C. *J. Chem. Soc. A* **1971**, 3300.
- (6) Abedini, M.; MacDiarmid, A. G. *Inorg. Chem.* **1963**, *2*, 608.
- (7) Aylett, B. J. *Adv. Inorg. Chem. Radiochem.* **1968**, *11*, 249.
- (8) Ebsworth, E. A. V. *Volatile Silicon Compounds*; Pergamon Press: New York, 1963; p 31.

[†] Present address: Indian Orchard Plant, Monsanto Chemical Co., Springfield, MA 01151.

of Me_3SnCl .⁹ $\text{SiF}_2\text{HSiF}_2\text{Br}$ was obtained from the reaction of SiF_4 with HBr ;¹¹ the redistribution of $\text{SiF}_2\text{HSiF}_2\text{Br}$ yielded $\text{SiF}_3\text{SiF}_2\text{H}$, $\text{SiF}_3\text{SiF}_2\text{HBr}$, and $\text{SiF}_3\text{SiHBr}_2$.¹¹ $\text{SiF}_3\text{SiHCl}_2$ and $\text{SiF}_2\text{HSiF}_2\text{Cl}$ were obtained from the reaction of SnCl_4 with $\text{SiF}_3\text{SiHBr}_2$ and $\text{SiF}_2\text{HSiF}_2\text{Br}$, respectively.¹² Unless otherwise noted, reactions involving Me_3SnH were performed on a vacuum line in the absence of solvent. The tin byproduct of these reactions was shown to be Me_3SnX ($\text{X} = \text{Br}, \text{Cl}$) by ^1H NMR and IR spectroscopy.¹³ Me_3SnX was removed from the disilanes by passing the mixtures through a trap cooled to -95°C (toluene), at which temperature the disilanes are volatile.

Spectral Measurements. The NMR tubes (5 mm o.d., wall thickness 0.77 mm) were flamed out under vacuum prior to loading. High-resolution ^1H and ^{19}F NMR spectra (toluene- d_6) were obtained on a Varian XL200 spectrometer operating at 200 and 188 MHz, respectively. Infrared spectra (gas cell, KBr windows, 2-cm^{-1} resolution) were obtained on a Nicolet 5SX Fourier transform spectrometer.

Reduction of $\text{SiF}_3\text{SiHBr}_2$ Using VITRIDE ($\text{NaAlH}_2(\text{OCH}_2\text{CH}_2\text{OC}_2\text{H}_5)_2$) or DIBAL-H ($i\text{-Bu}_2\text{AlH}$). The same procedure was used with each reducing agent. $\text{SiF}_3\text{SiHBr}_2$ (0.15 mmol) was condensed into a flask at -196°C and then warmed to -78°C (2-propanol/ CO_2). The reducing agent (0.15 mmol, in 15 mL of toluene) was added in portions over 30 min; no volatile compounds could be removed under vacuum at this point. The mixture was warmed to room temperature for 15 min. The volatile compounds were then removed under vacuum; an IR spectrum indicated the presence of SiH_4 (40%), SiF_3H (40%), and SiF_4 (20%; yields estimated from IR measurements). There were no disilanes present in the mixture.

Reduction of $\text{SiF}_3\text{SiHBr}_2$ Using LiAlH_4 . $\text{SiF}_3\text{SiHBr}_2$ (0.2 mmol) and LiAlH_4 (0.2 mmol) were allowed to react at room temperature for 15 min. An IR spectrum of the volatile material indicated the presence of SiF_3H (45%), SiH_4 (45%), SiH_3SiH_3 (5%),¹⁴ and unreacted $\text{SiF}_3\text{SiHBr}_2$ (5%; yields estimated from IR measurements).

Reduction of $\text{SiF}_3\text{SiHX}_2$ ($\text{X} = \text{Br}, \text{Cl}$) Using Me_3SnH . $\text{SiF}_3\text{SiHBr}_2$ (0.2 mmol) and Me_3SnH (0.4 mmol) were warmed to room temperature for 30 min; IR spectra indicated that the $\text{SiF}_3\text{SiHBr}_2$ had been consumed. Pure SiF_3SiH_3 , as determined from ^1H and ^{19}F NMR and IR spectra,^{11,15} was isolated in 90% yield. Comparable results were obtained with $\text{SiF}_3\text{SiHCl}_2$.

$\text{SiF}_3\text{SiHBr}_2$, Me_3SnH , and $\text{CF}_2=\text{CF}_2$ (1:2:7 ratio) at -196°C were warmed to room temperature for 10 min. An IR spectrum indicated the presence of only SiF_3SiH_3 and unreacted $\text{CF}_2=\text{CF}_2$.

One equivalent of $\text{SiF}_3\text{SiHCl}_2$ and 2 equiv of Me_3SnH were condensed into an NMR tube at -196°C . No reaction was observed via ^{19}F NMR as the tube was warmed to -10°C for 25 min. The tube was then warmed to 0°C and maintained at this temperature for 30 min. Very little $\text{SiF}_3\text{SiHCl}_2$ was observed in the mixture, the major component being SiF_3SiH_3 . There were also small peaks due to $\text{SiF}_3\text{SiH}_2\text{Cl}$.¹² After 1 h at 0°C , $\text{SiF}_3\text{SiHCl}_2$ and $\text{SiF}_3\text{SiH}_2\text{Cl}$ were consumed, with the major product being SiF_3SiH_3 (90% yield).

Reaction of $\text{SiF}_3\text{SiF}_2\text{HBr}$ with Me_3SnH . $\text{SiF}_3\text{SiF}_2\text{HBr}$ (0.2 mmol) and Me_3SnH (0.2 mmol) were allowed to react at room temperature for 10 min. ^1H and ^{19}F NMR and IR spectra indicated the presence of $\text{SiF}_3\text{-SiF}_2\text{H}$ ¹¹ and SiF_3SiH_3 in approximately equimolar amounts (90% isolated yield).

Equimolar quantities of $\text{SiF}_3\text{SiF}_2\text{HBr}$ and Me_3SnH were condensed into a 5-mm medium-wall NMR tube at -196°C . The mixture was warmed to -80°C for 30 min. The ^{19}F NMR spectrum contained peaks due to $\text{SiF}_3\text{SiF}_2\text{H}$ (major), SiF_3SiH_3 , $\text{SiF}_3\text{SiF}_2\text{H}$, and $\text{SiF}_3\text{SiHBr}_2$. A triplet centered at -122.9 ppm (relative to external CFCl_3) with $^3J_{\text{H-F}} = 7.7$ Hz was also present. The mixture was gradually warmed to 10°C ; the major products were SiF_3SiH_3 and $\text{SiF}_3\text{SiF}_2\text{H}$ (1:1 ratio, 90% yield), with small amounts of $\text{SiF}_3\text{SiF}_2\text{HBr}$ and $\text{SiF}_3\text{SiHBr}_2$ remaining.

Reaction of $\text{SiF}_2\text{HSiF}_2\text{X}$ ($\text{X} = \text{Br}, \text{Cl}$) with Me_3SnH . Equimolar quantities of $\text{SiF}_2\text{HSiF}_2\text{Br}$ and Me_3SnH were allowed to react at room temperature for 10 min. An IR spectrum indicated the major products

of the reaction to be $\text{SiF}_3\text{SiF}_2\text{H}$ and SiF_3SiH_3 (2:1 ratio, 90% yield). There were also absorptions in the Si-H stretching region at 2214 and 2198 cm^{-1} . Similar results were observed for $\text{SiF}_2\text{HSiF}_2\text{Cl}$.

Equimolar quantities of $\text{SiF}_2\text{HSiF}_2\text{Br}$ and Me_3SnH were condensed into a 5-mm medium-wall NMR tube at -196°C . The sample was gradually warmed to -40°C and held there for 20 min. Peaks due to $\text{SiF}_3\text{SiF}_2\text{H}$, $\text{SiF}_2\text{HSiF}_2\text{H}$,⁵ $\text{SiF}_3\text{SiF}_2\text{HBr}$, $\text{SiF}_3\text{SiHBr}_2$, and $\text{SiF}_2\text{BrSiF}_2\text{HBr}$ ¹¹ were observed. Most of the $\text{SiF}_2\text{HSiF}_2\text{Br}$ was gone after the mixture had been held at 10°C for 20 min. After 30 min at 20°C , the major products of the reaction were $\text{SiF}_3\text{SiF}_2\text{H}$ and SiF_3SiH_3 (2:1 ratio, 85% yield), together with equimolar quantities of $\text{SiF}_3\text{SiHBr}_2$, $\text{SiF}_3\text{SiH}_2\text{Br}$, $\text{SiF}_3\text{SiF}_2\text{HBr}$, and $\text{SiF}_2\text{HSiF}_2\text{H}$.

Results and Discussion

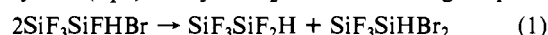
Fluorodisilanes of the general formula $\text{Si}_2\text{F}_x\text{H}_{6-x}$ were desired as precursors for the deposition of amorphous silicon films containing both hydrogen and fluorine. Our approach to these compounds involved the initial synthesis of bromo- or chlorofluorodisilanes and the subsequent selective conversion of Si-Br or Si-Cl into Si-H.

The reactions between $\text{SiF}_3\text{SiHBr}_2$ and various conventional reducing agents (LiAlH_4 , VITRIDE ($\text{NaAlH}_2(\text{OCH}_2\text{CH}_2\text{OC}_2\text{H}_5)_2$), and DIBAL ($i\text{-Bu}_2\text{AlH}$)) resulted in the cleavage of the Si-Si bond and reduction of some Si-F bonds. Although SiH_3SiH_3 was observed in the reactions with LiAlH_4 , no evidence was obtained for the formation of fluorodisilanes.

The reaction between $\text{SiF}_3\text{SiHX}_2$ ($\text{X} = \text{Br}, \text{Cl}$) and Me_3SnH (1:2 molar ratio) proceeded smoothly at room temperature to yield SiF_3SiH_3 in 90% yield. There was no evidence for further reaction of SiF_3SiH_3 with Me_3SnH . A low-temperature ^{19}F NMR experiment (where $\text{X} = \text{Cl}$) indicated that these reductions proceed in a stepwise manner, as evidenced by observation of $\text{SiF}_3\text{SiH}_2\text{Cl}$.¹² SiF_3SiH_3 has previously been observed as a member of a complex mixture of products resulting from the reaction of SiF_2 and B_2H_6 .¹⁵ A two-step separation process then had to be used to obtain pure SiF_3SiH_3 .

The corresponding reaction of $\text{SiF}_3\text{SiF}_2\text{HBr}$ with Me_3SnH was expected to provide the previously unknown molecule $\text{SiF}_3\text{SiFH}_2$. However, when equimolar amounts of $\text{SiF}_3\text{SiF}_2\text{HBr}$ and Me_3SnH were allowed to react at room temperature, the products consisted of $\text{SiF}_3\text{SiF}_2\text{H}$ and SiF_3SiH_3 in a 1:1 molar ratio (90% yield). There was no evidence of other disilanes in the product mixture. A possible explanation for this behavior is that $\text{SiF}_3\text{SiFH}_2$ is initially formed but that it quickly undergoes redistribution to give the observed products. Such behavior would parallel that of fluorosilane, which has been described as being very susceptible to F/H bond redistribution.⁸

Mechanistic insight into this reaction was provided by a low-temperature ^{19}F NMR experiment. $\text{SiF}_3\text{SiF}_2\text{HBr}$ and Me_3SnH were condensed into an NMR tube at -196°C and warmed to -80°C for 30 min. An NMR spectrum obtained at this point indicated the presence of $\text{SiF}_3\text{SiF}_2\text{HBr}$, SiF_3SiH_3 , $\text{SiF}_3\text{SiF}_2\text{H}$, and $\text{SiF}_3\text{SiHBr}_2$. A triplet centered at -122.9 ppm (relative to external CFCl_3) with $^3J_{\text{H-F}} = 7.7$ Hz is very similar to that observed for $\text{SiF}_3\text{SiH}_2\text{Cl}$ ¹² and is assigned to $\text{SiF}_3\text{SiH}_2\text{Br}$. There was no direct evidence for the formation of $\text{SiF}_3\text{SiFH}_2$ even at this low temperature. The presence of $\text{SiF}_3\text{SiHBr}_2$ indicates that the starting material undergoes F/Br redistribution reactions prior to reduction by the tin hydride (eq 1). $\text{SiF}_3\text{SiHBr}_2$ could then undergo stepwise



reduction (via $\text{SiF}_3\text{SiH}_2\text{Br}$) to the observed SiF_3SiH_3 .

In the absence of Me_3SnH , $\text{SiF}_3\text{SiF}_2\text{HBr}$ requires several hours at room temperature to undergo redistribution to form $\text{SiF}_3\text{SiF}_2\text{H}$ and $\text{SiF}_3\text{SiHBr}_2$. This observation suggests that Me_3SnH is promoting redistribution (eq 1), even at -80°C . Conversion of Si-Br into Si-H by the tin hydrides occurs only after this redistribution has occurred.

The reaction between $\text{SiF}_2\text{HSiF}_2\text{Br}$ and Me_3SnH was also investigated. An infrared spectrum of the products of a room-temperature reaction indicated the presence of $\text{SiF}_3\text{SiF}_2\text{H}$ and SiF_3SiH_3 (2:1 ratio, 90% yield). There was also an absorption in the Si-H stretching region at 2214 cm^{-1} ; this feature is tentatively assigned to $\text{SiF}_2\text{BrSiF}_2\text{HBr}$, given the similarity of this

- (9) (a) Dillard, C. R.; May, L. J. *Mol. Spectrosc.* **1964**, *14*, 250. (b) Maddox, M. L.; Flitcroft, N.; Kaesz, H. D. *J. Organomet. Chem.* **1965**, *4*, 50. (c) Potter, P. E.; Pratt, L.; Wilkinson, G. *J. Chem. Soc.* **1964**, 524.
- (10) (a) Margrave, J. L.; Sharp, K. G.; Wilson, P. W. *Fortschr. Chem. Forsch.* **1972**, *26*, 1. (b) Perry, D. L.; Margrave, J. L. *J. Chem. Educ.* **1976**, *53*, 696. (c) Margrave, J. L.; Wilson, P. W. *Acc. Chem. Res.* **1971**, *4*, 145.
- (11) Sharp, K. G.; Bald, J. F., Jr. *Inorg. Chem.* **1975**, *14*, 2553.
- (12) D'Errico, J. J.; Sharp, K. G. *Main Group Met. Chem.*, in press.
- (13) (a) Neumann, W. P. *The Organic Chemistry of Tin*; Interscience: New York, 1970. (b) Kupchik, E. J. *Organotin Compounds*; Sawyer, A. K., Ed.; Marcel Dekker: New York, 1971.
- (14) Bethke, G. W.; Wilson, M. K. *J. Chem. Phys.* **1957**, *26*, 1107.
- (15) Solan, D.; Burg, A. B. *Inorg. Chem.* **1972**, *11*, 1253.

Contribution from the Chemistry Department,
The Chinese University of Hong Kong,
Shatin, NT, Hong Kong

stretching frequency to that of $\text{SiF}_3\text{SiFHBr}$ (2216 cm^{-1}). A second absorption at 2198 cm^{-1} could be due to a compound such as $\text{SiF}_3\text{SiH}_2\text{Br}$, as this frequency lies between the Si-H stretches of SiF_3SiH_3 (2189 cm^{-1}) and $\text{SiF}_3\text{SiHBr}_2$ (2203 cm^{-1}).¹⁶

A low-temperature ^{19}F NMR experiment revealed a rather complex series of reactions. As was the case for $\text{SiF}_3\text{SiFHBr}$, this reaction is characterized by the initial F/Br redistribution of the starting $\text{SiF}_2\text{HSiF}_2\text{Br}$. A complicating factor is the availability of both ends of $\text{SiF}_2\text{HSiF}_2\text{Br}$ for redistribution (for $\text{SiF}_3\text{SiFHBr}$, SiF_3 is inert with respect to redistribution). The redistribution of $\text{SiF}_2\text{HSiF}_2\text{Br}$ leads to the formation of $\text{SiF}_3\text{SiF}_2\text{H}$, $\text{SiF}_2\text{BrSiFHBr}$, $\text{SiF}_3\text{SiFHBr}$, and $\text{SiF}_3\text{SiHBr}_2$.¹¹ Additionally, the direct reduction of the starting material to $\text{SiF}_2\text{HSiF}_2\text{H}$ appears to proceed at a competitive rate, as a small amount of this compound was observed in the early stages of this reaction.

It was thought that the corresponding redistribution reactions would be slower for $\text{SiF}_2\text{HSiF}_2\text{Cl}$, thus allowing the isolation of $\text{SiF}_2\text{HSiF}_2\text{H}$. However, comparable results were obtained in the reactions of $\text{SiF}_2\text{HSiF}_2\text{Br}$ or $\text{SiF}_2\text{SiF}_2\text{Cl}$ with Me_3SnH .

Organotin hydrides typically react with organic halides and unsaturated bonds via a free-radical mechanism. These reactions require heating, irradiation, or initiation by a free-radical source.¹⁷ However, in the case of the bromo- or chlorofluorodisilanes, the reactions proceeded below room temperature and in the absence of free-radical initiators. There was no evidence of Si-Si bond cleavage or products attributable to coupling of free radicals. Additionally, the reaction of $\text{SiF}_3\text{SiHBr}_2$ with Me_3SnH was unaffected by the presence of $\text{CF}_2=\text{CF}_2$; under free-radical conditions, products attributable to the addition of Me_3SnH to the olefin should be apparent.¹⁸ A mechanism that is consistent with these observations involves a four-centered transition state in which there is a pairwise exchange of atoms between the silicon and tin. This type of transition state has been postulated for other reductions involving Me_3SnH ¹⁹ and for the F-Br exchange observed between disilane molecules.¹¹

Other reactions of alkyltin hydrides have been suggested to proceed via nucleophilic attack of the tin hydride, resulting in a polar transition state.²⁰ However, these reactions are promoted by the presence of polar solvents. Since the reactions involving halofluorodisilanes can occur in the gas phase, we do not feel that polar transition states play an important role in these reactions.

Conclusions

SiF_3SiH_3 is obtained in 90% yield from the reaction of $\text{SiF}_3\text{SiHX}_2$ ($X = \text{Br}, \text{Cl}$) with 2 equiv of Me_3SnH . F/Br redistribution precedes reduction in reactions between $\text{SiF}_3\text{SiFHBr}$ and Me_3SnH , resulting in mixtures of $\text{SiF}_3\text{SiF}_2\text{H}$ and SiF_3SiH_3 (1:1 ratio, 90% yield). The reaction of $\text{SiF}_2\text{HSiF}_2\text{X}$ ($X = \text{Br}, \text{Cl}$) with Me_3SnH also led to mixtures of $\text{SiF}_3\text{SiF}_2\text{H}$ and SiF_3SiH_3 (2:1 ratio) in 85-90% yield; small amounts of $\text{SiF}_2\text{HSiF}_2\text{H}$ (<5%) were also observed.

Acknowledgment. We wish to thank the Solar Energy Research Institute for support of this work through Contract No. ZL-5-04074-6.

Registry No. $\text{SiF}_3\text{SiHBr}_2$, 56144-86-6; $\text{NaAlH}_2(\text{OCH}_2\text{CH}_2\text{OCH}_3)_2$, 22722-98-1; $i\text{-Bu}_2\text{AlH}$, 1191-15-7; SiH_4 , 7803-62-5; SiF_3H , 13465-71-9; SiF_4 , 7783-61-1; LiAlH_4 , 16853-85-3; SiH_3SiH_3 , 1590-87-0; $\text{SiF}_3\text{SiHCl}_2$, 119895-84-0; Me_3SnH , 1631-73-8; $\text{CF}_2=\text{CF}_2$, 116-14-3; $\text{SiF}_3\text{SiH}_2\text{Cl}$, 121097-51-6; $\text{SiF}_3\text{SiFHBr}$, 56144-87-7; $\text{SiF}_3\text{SiF}_2\text{H}$, 24628-33-9; SiF_3SiH_3 , 15195-26-3; $\text{SiF}_2\text{HSiF}_2\text{Br}$, 51040-08-5; $\text{SiF}_2\text{HSiF}_2\text{Cl}$, 119895-86-2; $\text{SiF}_2\text{HSiF}_2\text{H}$, 34669-37-9; $\text{SiF}_2\text{BrSiFHBr}$, 56144-88-8; $\text{SiF}_3\text{SiH}_2\text{Br}$, 121097-52-7.

- (16) Excellent correlations between Si-H stretching frequencies and the functionality on silicon have been observed. See: Smith, A. L. In *Chemical, Biological and Industrial Applications of Infrared Spectroscopy*; Durig, J. R., Ed.; Wiley-Interscience: New York, 1985.
- (17) Kuivila, H. G. *Synthesis* 1970, 499.
- (18) Clark, H. C.; Furnival, S. G.; Kwon, J. T. *Can. J. Chem.* 1963, 41, 2889.
- (19) Dehnert, P.; Grobe, J.; Le Van, D. Z. *Naturforsch.* 1981, 36B, 48.
- (20) (a) Gaines, D. F.; Kunz, J. C.; Kulzick, M. J. *Inorg. Chem.* 1985, 24, 3336. (b) Emery, S. L.; Morrison, J. A. *Inorg. Chem.* 1985, 24, 1613. (c) Leusink, A. J.; Marsman, J. W. *Recl. Trav. Chim. Pays-Bas* 1965, 84, 1123.

Theoretical Study of the Structures, Relative Stabilities, and Infrared Spectra of the Isomeric NSO^- Anions

Suk Ping So

Received October 17, 1988

The potassium salt of the NSO^- anion was first prepared and characterized by vibrational spectroscopy about 10 years ago by Armitage and Brand.¹ They suggested that this anion be called the thiataze ion. However, the synthesis, spectroscopic data, and X-ray structure of the isovalent thionitrite anion SNO^- (as the $(\text{Ph}_2\text{P})_2\text{N}^+$ salt) were reported only recently.²

To compare the structures, stabilities, and spectroscopic properties of the above two isomeric anions, Chivers et al.³ have carried out a calculation on their structures. They optimized the bond angles of NSO^- and SNO^- by the MNDO method, fixing the bond lengths at those for $(\text{Ph}_2\text{P})_2\text{N}^+\text{SNO}^-$ obtained from X-ray diffraction analysis. Then a single-point ab initio calculation was done to compute the orbital eigenvalues and Mulliken's populations by using the double- ζ basis (i.e. each atomic orbital is represented by two basis functions) of Clementi and Roetti⁴ augmented with a 3d polarization function on sulfur (DZ+d(S)).⁵ In fact, the equilibrium geometries and relative stabilities of NSO^- and SNO^- have been computed earlier by Ehrhardt and Ahlrichs⁶ using the ab initio SCF method and basis sets of better than double- ζ plus polarization functions quality.

To the author's knowledge, the other isomeric anions SON^- and cyclic cy- NSO^- are still not known. In addition, infrared data for SNO^- are lacking. Hence, a theoretical study on the structures and infrared spectra of these four isomeric anions was carried out in the hope that this work may be helpful to their future experimental identification. The optimized geometries of NSO^- and SNO^- , though reported earlier,⁶ were recalculated because it is more consistent to discuss and compare results of these anions obtained with the same basis set.

Calculations

The structures of NSO^- , SNO^- , SON^- , and cy- NSO^- were fully optimized by the energy gradient method using the GAUSSIAN 82 and Gaussian 86 packages of programs.⁷ The standard 6-31G* and 6-31+G* basis functions were used. (A 6-31G split-valence basis set utilizes the expansion of six Gaussian functions for each inner-shell atomic orbital and, for each valence atomic orbital, two valence shells comprising three and one Gaussian functions, respectively. A 6-31G* basis set results when a set of six d-type functions for the second-row atom is added.) The extra electron in an anion is usually weakly bound. Even large basis sets such as 6-31G* do not incorporate functions with significant amplitude at a distance from their center and thus do not provide a completely adequate description of molecular species in which a large portion of the valence electron density is allocated to diffuse lone-pair or to antibonding orbitals. One way to overcome problems associated with anion calculations is to include in the basis set one or more highly diffuse functions, such as the 6-31+G* set, which is the 6-31G* set augmented by a single set of diffuse Gaussian s- and p-type functions for each of the constituent atoms.⁸ These basis functions are then able to describe properly the

- (1) Armitage, D. A.; Brand, J. C. *J. Chem. Soc., Chem. Commun.* 1979, 1078.
- (2) Seel, F.; Kuhn, R.; Simon, G.; Wagner, M.; Krebs, B.; Dartmann, M. *Z. Naturforsch.* 1985, 40B, 1607.
- (3) Chivers, T.; Silva, A. B. F. D.; Treu, O., Jr.; Trsic, M. *J. Mol. Struct.* 1987, 162, 351.
- (4) Clementi, E.; Roetti, A. *At. Data Nucl. Data Tables* 1974, 14, 177.
- (5) Laidlaw, W. G.; Trsic, M. *Chem. Phys.* 1979, 36, 323.
- (6) Ehrhardt, C.; Ahlrichs, R. *Chem. Phys.* 1986, 108, 417.
- (7) (a) Binkley, J. S.; Frisch, M. J.; DeFrees, D. J.; Raghavachari, K.; Whiteside, R. A.; Schlegel, H. B.; Fluder, E. M.; Pople, J. A. "GAUSSIAN 82"; Carnegie-Mellon University: Pittsburgh, PA, 1983. (b) Frisch, M. J.; Binkley, J. S.; Schlegel, H. B.; Raghavachari, K.; Melius, C. F.; Seeger, R.; Whiteside, R. A.; Fox, D. J.; Fluder, E. M.; Pople, J. A. "Gaussian 86"; Carnegie-Mellon Quantum Chemistry Publishing Unit: Pittsburgh PA, 1984.